

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		10/065,920	VOLLERTSEN, ROLF-P.	
Examiner		Art Unit		Page 1 of 1
Anjan K Deb		2858		

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	C	US-			
	D	US-			
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	F	US-			
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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